

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKiiP 12NAB126V1

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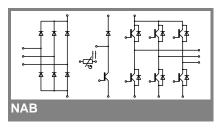
- Fast Trench IGBTs
- · Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 10 kVATypical motor power 5,5 kW

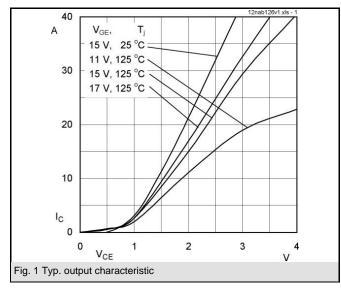
Remarks

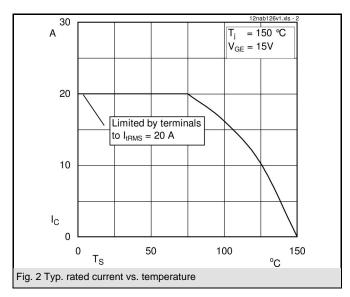
• V_{CEsat}, V_F = chip level value

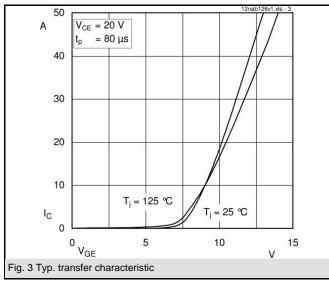


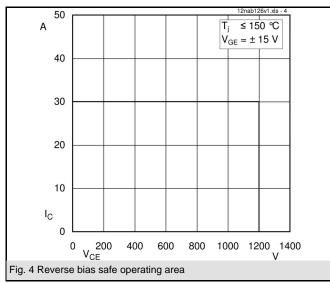
Absolute Maximum Ratings $T_s = 25 ^{\circ}\text{C}$, unless otherwise specific						
Symbol	Conditions	Values	Units			
IGBT - Inverter, Chopper						
V_{CES}		1200	V			
I _C	T _s = 25 (70) °C	28 (22)	Α			
I _{CRM}		30	Α			
V_{GES}		± 20	V			
T_j		- 40 + 150	°C			
Diode - Inverter, Chopper						
I _F	T _s = 25 (70) °C	26 (20)	Α			
I _{FRM}		30	Α			
T _j		- 40 + 150	°C			
Diode - Rectifier						
V_{RRM}		1600	V			
I _F	T _s = 70 °C	35	Α			
I _{FSM}	t _p = 10 ms, sin 180 °, T _j = 25 °C	220	Α			
i²t	t _p = 10 ms, sin 180 °, T _i = 25 °C	240	A²s			
T _j	,	- 40 + 150	°C			
Module	1		1			
I _{tRMS}	per power terminal (20 A / spring)	20	Α			
T _{stg}		- 40 + 125	°C			
V _{isol}	AC, 1 min.	2500	V			

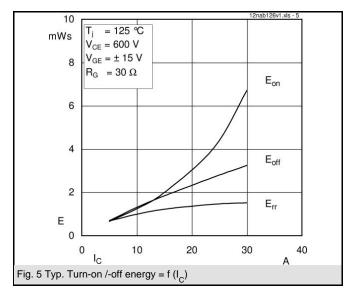
Characte	ristics	s = 25 °C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units			
IGBT - Inverter, Chopper								
V_{CEsat}	I _{Cnom} = 15 A, T _i = 25 (125) °C		1,7 (2)	2,1 (2,4)	V			
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0.6$ mA	5	5,8	6,5	V			
V _{CE(TO)}	T _j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V			
r _T	T _j = 25 (125) °C		47 (73)	60 (87)	mΩ			
C _{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		1		nF			
C _{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,1		nF			
C _{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,1		nF			
$R_{th(j-s)}$	per IGBT		1,15		K/W			
t _{d(on)}	under following conditions		25		ns			
t _r `´	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		25		ns			
$t_{d(off)}$	$I_{Cnom} = 15 \text{ A}, T_j = 125^{\circ}\text{C}$		385		ns			
t _f	$R_{Gon} = R_{Goff} = 30 \Omega$		90		ns			
E _{on}	inductive load		2		mJ			
E_{off}			1,9		mJ			
Diode - Ir	verter, Chopper							
$V_F = V_{EC}$	I _{Fnom} = 15 A, T _i = 25 (125) °C		1,6 (1,6)	1,8 (1,8)	V			
V _(TO)	T _i = 25 (125) °C		1 (0,8)	1,1 (0,9)	V			
r _T	T _i = 25 (125) °C		40 (53)	47 (60)	mΩ			
$R_{th(j-s)}$	per diode		1,95		K/W			
I _{RRM}	under following conditions		25		Α			
Q_{rr}	I _{Fnom} = 15 A, V _R = 600 V		3		μC			
E _{rr}	V _{GE} = 0 V, T _i = 125 °C		1,3		mJ			
	$di_F/dt = 900 \text{ A/}\mu\text{s}$							
Diode - R	ectifier	•			•			
V _F	I _{Fnom} = 15 A, T _j = 25 °C		1,1		V			
V _(TO)	T _i = 150 °C	0,8			V			
r _T	T _i = 150 °C	20			mΩ			
$R_{th(j-s)}$	per diode		1,5		K/W			
	ture Sensor							
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω			
Mechanical Data								
w			35		g			
M_s	Mounting torque	2		2,5	Nm			

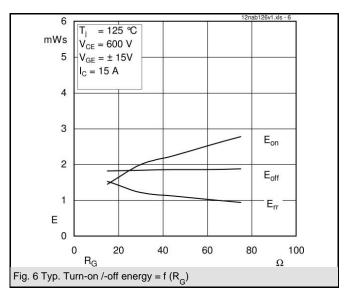


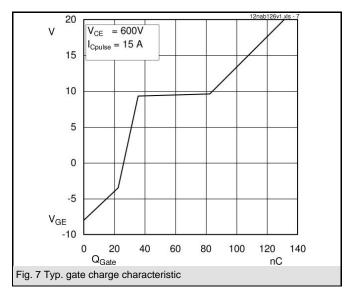


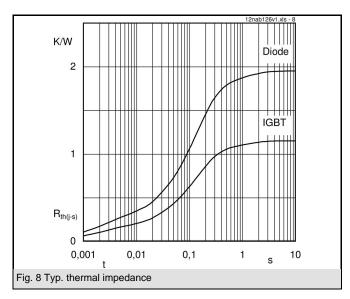


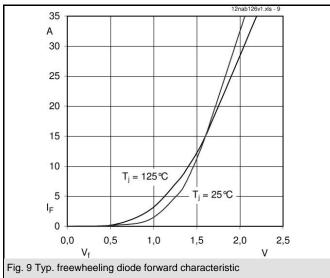


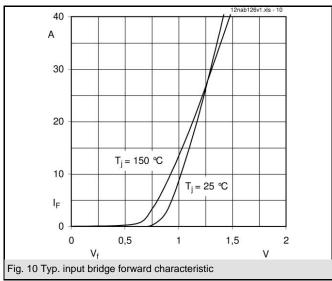




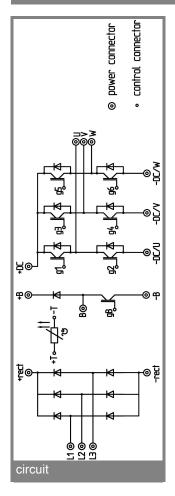


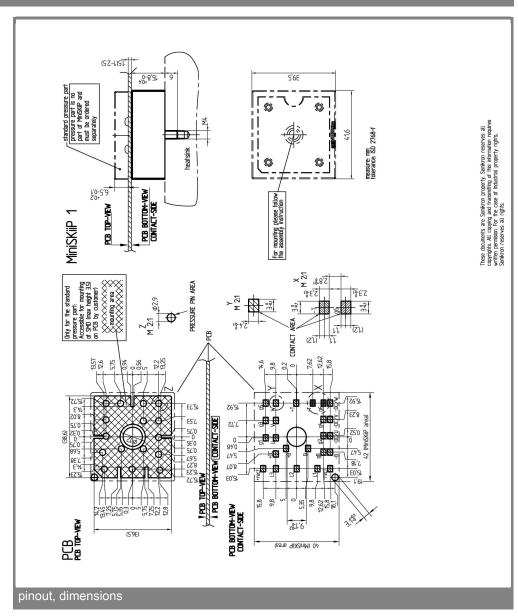






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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

^{*} The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.